

isc N-Channel MOSFET Transistor

PSMN4R8-100BSEJ

FEATURES

- Drain Current : I_D= 120A@ T_C=25℃
- Drain Source Voltage
 - : V_{DSS}= 100V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 4.8 \text{m} \Omega \text{ (Max)} @ V_{GS} = 10 \text{V}$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

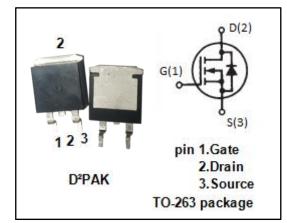
 motor drive, DC-DC converter, power switch and solenoid drive.

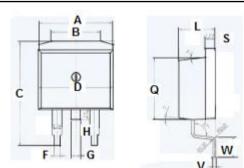
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT			
$V_{ extsf{DSS}}$	Drain-Source Voltage	100	V			
V _{GS}	Gate-Source Voltage-Continuous	±20	V			
I _D	Drain Current-Continuous	120	А			
І _{ОМ}	Drain Current-Single Pluse	707	А			
P _D	Total Dissipation @T _C =25℃	405	W			
TJ	Max. Operating Junction Temperature	-55~175	$^{\circ}$			
T _{stg}	Storage Temperature	-55~175	$^{\circ}$			

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.37	°C/W





DIM	m	m
DIIVI	MIN	MAX
Α	9.8	10.2
В	6.6	6.8
С	15.1	15.3
D	9.6	10
F	0.7	0.9
G	1.26	1.3
Н	1.2	1.45
L	4.4	4.6
Q	9.2	9.3
S	1.25	1.35
V	0.4	0.6
W	2.6	2.8

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	100		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D = 0.25mA	2.0	4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 25A		4.8	m Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V;V _{DS} = 0		±0.1	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V; V _{GS} = 0		10	uA
V _{SD}	Forward On-Voltage	I _S = 25A; V _{GS} = 0		1.2	V



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